## A3959

# DMOS Full-Bridge PWM Motor Driver

#### **Selection Guide**

Part Number	Package	Packing
A3959SB-T	24-pin DIP with exposed tabs	15 per tube
A3959SLB-T	24-pin SOIC with internally fused pins	31 per tube
A3959SLBTR-T	24-pin SOIC with internally fused pins	1000 per reel
A3959SLP-T	28-pin TSSOP with exposed thermal pad	50 per tube
A3959SLPTR-T	28-pin TSSOP with exposed thermal pad	4000 per reel

#### **Absolute Maximum Ratings**

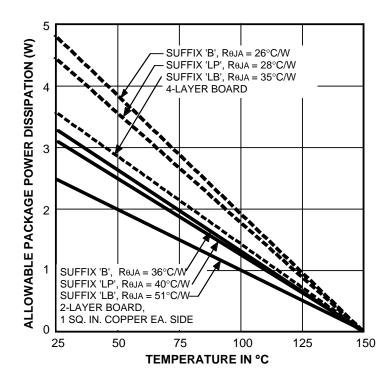
Characteristic	Symbol	Notes	Rating	Units	
Load Supply Voltage	V <sub>BB</sub>		50	V	
Logic Supply Voltage	V <sub>DD</sub>			7.0	٧
Innut Valtage		Continuous		-0.3 to V <sub>DD</sub> + 0.3	V
Input Voltage	V <sub>IN</sub>	t <sub>w</sub> < 30 ns		-1.0 to V <sub>DD</sub> + 1.0	V
0	.,	Continuous	Continuous		V
Sense Voltage	V <sub>S</sub>	t <sub>w</sub> < 3 µs		2.5	V
Reference Voltage	V <sub>REF</sub>			$V_{DD}$	V
Output Current	1	Output current rating may be limited by duty cycle, ambient temperature, and heat sinking. Under any set of	Repetitive	±3.0	Α
Output Ourient	Гоит	conditions, do not exceed the specified current rating or a junction temperature of 150°C.	Peak, < 3 µs	±6.0	Α
Package Power Dissipation	P <sub>D</sub>	See Thermal Characteristics		_	_
Operating Ambient Temperature	T <sub>A</sub>	Range S	-20 to 85	°C	
Maximum Junction Temperature	T <sub>J</sub> (max)	Fault conditions that produce excessive junction temper the device's thermal shutdown circuitry. These condition ated but should be avoided.	150	°C	
Storage Temperature	T <sub>stg</sub>			-55 to 150	°C



#### **Thermal Characteristics**

Characteristic	Symbol		Test Conditions		Units
		B package	B package		W
Package Power Dissipation	$P_{D}$	LB package		2.5	W
		LP package		3.1	W
			1-layer PCB, minimal exposed copper area	54	°C/W
		B Package	2-layer PCB, 1-in <sup>2</sup> 2-oz copper exposed area	36	°C/W
	R <sub>θJA</sub>		4-layer PCB, based on JEDEC standard	26	°C/W
		LB Package	1-layer PCB, minimal exposed copper area	77	°C/W
Package Thermal Resistance, Junction to Ambient			2-layer PCB, 1-in <sup>2</sup> 2-oz copper exposed area	51	°C/W
			4-layer PCB, based on JEDEC standard	35	°C/W
			1-layer PCB, minimal exposed copper area	100	°C/W
		LP Package	2-layer PCB, 1-in <sup>2</sup> 2-oz copper exposed area	40	°C/W
			4-layer PCB, based on JEDEC standard	28	°C/W
Package Thermal Resistance, Junction to Tab	$R_{\theta JT}$	B and LB pac	kages	6	°C/W
Package Thermal Resistance, Junction to Pad	$R_{\theta JP}$	LP package		2	°C/W

<sup>\*</sup>Additional thermal information available on Allegro website.





3

# ELECTRICAL CHARACTERISTICS at $T_A$ = +25°C, $V_{BB}$ = 50 V, $V_{DD}$ = 5.0 V, $V_{SENSE}$ = 0.5 V, $f_{PWM}$ < 50 kHz (unless noted otherwise)

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Output Drivers						
Load Supply Voltage Bangs	N/	Operating	9.5 –	50	V	
Load Supply Voltage Range	V <sub>BB</sub>	During sleep mode	0	_	50	V
Output Leakage Current		$V_{OUT} = V_{BB}$	_	<1.0	20	μA
Output Leakage Current	I <sub>DSS</sub>	V <sub>OUT</sub> = 0 V	_	<-1.0	-20	μA
Output On Resistance	r	Source driver, I <sub>OUT</sub> = -3 A	_	270	300	mΩ
Output Off Resistance	r <sub>DS(on)</sub>	Sink driver, I <sub>OUT</sub> = 3 A	_	270	300	mΩ
Crossover Delay			300	600	1000	ns
Body Diode Forward Voltage	V <sub>F</sub>	Source diode, I <sub>F</sub> = -3 A	_	-	1.6	V
Body Blode Folward Voltage	v <sub>F</sub>	Sink diode, I <sub>F</sub> = 3 A	_	_	1.6	V
		f <sub>PWM</sub> < 50 kHz	_	4.0	7.0	mA
Load Supply Current	I <sub>BB</sub>	Charge pump on, outputs disabled	_	2.0	5.0	mA
		Sleep mode	-	_	20	μA
Control Logic						
Logic Supply Voltage Range	$V_{DD}$	Operating	4.5	5.0	5.5	V
Logic Input Voltage	V <sub>IN(1)</sub>		2.0	-	_	V
Logic iriput voitage	V <sub>IN(0)</sub>		_	-	8.0	V
Logic Input Current	I <sub>IN(1)</sub>	V <sub>IN</sub> = 2.0 V	_	<1.0	20	μA
(all inputs except ENABLE)	I <sub>IN(0)</sub>	V <sub>IN</sub> = 0.8 V	_	<-2.0	-20	μA
Logic Supply Current		f <sub>PWM</sub> < 50 kHz	_	6.0	10	mA
Logic Supply Current	I <sub>DD</sub>	Sleep mode	_	_	2.0	mA
ENABLE Input Current	I <sub>IN(1)</sub>	V <sub>IN</sub> = 2.0 V	_	40	100	μA
ENABLE Input Current	I <sub>IN(0)</sub>	V <sub>IN</sub> = 0.8 V	_	16	40	μA
Internal OSC fraguency	f	ROSC shorted to GROUND	3.25	4.25	5.25	MHz
Internal OSC frequency	fosc	ROSC = 51 kΩ	3.65	4.25	4.85	MHz
Reference Input Volt. Range	V <sub>REF</sub>	Operating	0.0	_	$V_{DD}$	V
Reference Input Current	I <sub>REF</sub>	$V_{REF} = V_{DD}$	_	_	±1.0	μA
Comparator Input Offset Voltage	V <sub>IO</sub>	V <sub>REF</sub> = 0 V	_	±5.0	_	mV

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## ELECTRICAL CHARACTERISTICS (continued) at $T_A = +25$ °C, $V_{BB} = 50$ V, $V_{DD} = 5.0$ V, $V_{SENSE} = 0.5$ V, f<sub>PWM</sub> < 50 kHz (unless noted otherwise)

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Reference Divider Ratio	_		_	10	_	_
Gm Error	Е	$V_{REF} = V_{DD}$	_	_	±4.0	%
(Note 3)	E <sub>Gm</sub>	V <sub>REF</sub> = 0.5 V	_	_	±14	%
		0.5 E <sub>in</sub> to 0.9 E <sub>out</sub> :				
	t <sub>pd</sub>	PWM change to source on	600	750	1200	ns
Propagation Delay Times		PWM change to source off	50	150	350	ns
		PWM change to sink on	600	750	1200	ns
		PWM change to sink off	50	100	150	ns
Thermal Shutdown Temp.	T <sub>J</sub>		_	165	_	°C
Thermal Shutdown Hysteresis	$\DeltaT_J$		_	15	_	°C
UVLO Enable Threshold	UVLO	Increasing V <sub>DD</sub>	3.90	4.2	4.45	V
UVLO Hysteresis	ΔUVLO		0.05	0.10	_	V

NOTES:

- 1. Typical Data is for design information only.
- 2. Negative current is defined as coming out of (sourcing) the specified device terminal.
- 3.  $G_m$  error = ([ $V_{REF}/10$ ]  $V_{SENSE}$ )/( $V_{REF}/10$ ) where  $V_{SENSE}$  =  $I_{TRIP} \cdot R_S$ .



5

#### **FUNCTIONAL DESCRIPTION**

**V**<sub>REG</sub>. This internally generated voltage is used to operate the sink-side DMOS outputs. The V<sub>REG</sub> terminal should be decoupled with a 0.22  $\mu$ F capacitor to ground.  $V_{REG}$  is internally monitored and in the case of a fault condition, the outputs of the device are disabled.

**Charge Pump.** The charge pump is used to generate a gate-supply voltage greater than V<sub>BB</sub> to drive the sourceside DMOS gates. A 0.22 µF ceramic capacitor should be connected between CP1 and CP2 for pumping purposes. A 0.22 µF ceramic capacitor should be connected between CP and V<sub>BB</sub> to act as a reservoir to operate the high-side DMOS devices. The CP voltage is internally monitored and, in the case of a fault condition, the source outputs of the device are disabled.

**PHASE Logic.** The PHASE input terminal determines if the device is operating in the "forward" or "reverse" state.

PHASE	OUT <sub>A</sub>	OUTB	
0	Low	High	
1	High	Low	

**ENABLE Logic.** The ENABLE input terminal allows external PWM. ENABLE high turns on the selected sinksource pair. ENABLE low switches off the source driver or the source and sink driver, depending on EXT MODE, and the load current decays. If ENABLE is kept high, the current will rise until it reaches the level set by the internal current-control circuit.

ENABLE	Outputs	
0	Chopped	
1	On	

**EXT MODE Logic.** When using external PWM current control, the EXT MODE input determines the current path during the chopped cycle. With EXT MODE low, fast decay mode, the opposite pair of selected outputs will be enabled during the off cycle. With EXT MODE high, slow decay mode, both sink drivers are on with ENABLE low.

EXT MODE	Decay	
0	Fast	
1	Slow	

**Current Regulation.** Load current is regulated by an internal fixed off-time PWM control circuit. When the outputs of the DMOS H bridge are turned on, the current increases in the motor winding until it reaches a trip value determined by the external sense resistor  $(R_s)$  and the applied analog reference voltage  $(V_{REF})$ :

$$I_{TRIP} = V_{REF}/10R_{S}$$

At the trip point, the sense comparator resets the sourceenable latch, turning off the source driver. The load inductance then causes the current to recirculate for the fixed off-time period. The current path during recirculation is determined by the configuration of slow/mixed/fast current-decay mode via PFD1 and PFD2.

**Oscillator.** The PWM timer is based on an internal oscillator set by a resistor connected from the R<sub>OSC</sub> terminal to V<sub>DD</sub>. Typical value of 4 MHz is set with a 51 k $\Omega$  resistor. The allowable range of the resistor is from  $20 \text{ k}\Omega$  to  $100 \text{ k}\Omega$ .

$$f_{OSC} = 204 \text{ x } 10^9 / R_{OSC}.$$

If  $R_{OSC}$  is not pulled up to  $V_{DD}$ , it must be shorted to ground.

**Fixed Off Time.** The A3959 is set for a fixed off time of 96 cycles of the internal oscillator, typically 24 µs with a 4 MHz oscillator.



6

## **FUNCTIONAL DESCRIPTION** (continued)

Internal Current-Control Mode. Inputs PFD1 and PFD2 determine the current-decay method after an overcurrent event is detected at the SENSE input. In slowdecay mode, both sink drivers are turned on for the fixed off-time period. Mixed-decay mode starts out in fast-decay mode for a portion (15% or 48%) of the fixed off time, and then is followed by slow decay for the remainder of the period.

PFD2	PFD1	% t <sub>off</sub>	Decay
0	0	0	Slow
0	1	15	Mixed
1	0	48	Mixed
1	1	100	Fast

**PWM Blank Timer.** When a source driver turns on, a current spike occurs due to the reverse-recovery currents of the clamp diodes and/or switching transients related to distributed capacitance in the load. To prevent this current spike from erroneously resetting the source-enable latch, the sense comparator is blanked. The blank timer runs after the off-time counter to provide the blanking function. The blank timer is reset when ENABLE is chopped or PHASE is changed. For external PWM control, a PHASE change or ENABLE on will trigger the blanking function. The duration is determined by the BLANK input and the oscilator.

BLANK	t <sub>blank</sub>
0	6/f <sub>osc</sub>
1	12/f <sub>osc</sub>

Synchronous Rectification. When a PWM off cycle is triggered, either by an ENABLE chop command or internal fixed off-time cycle, load current will recirculate according to the decay mode selected by the control logic. The A3959 synchronous rectification feature will turn on

the appropriate pair of DMOS outputs during the current decay and effectively short out the body diodes with the low r<sub>DS(on)</sub> driver. This will reduce power dissipation significantly and can eliminate the need for external Schottky diodes.

Synchronous rectification will prevent reversal of load current by turning off all outputs when a zero-current level is detected.

**Shutdown.** In the event of a fault (excessive junction temperature, or low voltage on CP or V<sub>REG</sub>) the outputs of the device are disabled until the fault condition is removed. At power up, and in the event of low V<sub>DD</sub>, the UVLO circuit disables the drivers.

**Braking.** The braking function is implemented by driving the device in slow-decay mode via EXTMODE and applying an enable chop command. Because it is possible to drive current in either direction through the DMOS drivers, this configuration effectively shorts out the motor-generated BEMF as long as the ENABLE chop mode is asserted. It is important to note that the internal PWM current-control circuit will not limit the current when braking, because the current does not flow through the sense resistor. The maximum brake current can be approximated by  $V_{\mbox{\footnotesize BEMF}}/R_{\mbox{\footnotesize L}}.$  Care should be taken to ensure that the maximum ratings of the device are not exceeded in worst-case braking situations of high speed and high inertial loads.

**SLEEP Logic.** The SLEEP input terminal is used to minimize power consumption when when not in use. This disables much of the internal circuitry including the regulator and charge pump. Logic low will put the device into sleep mode, logic high will allow normal operation.

Note: If the sleep mode is not used, connect a 5 k $\Omega$  pullup resistor between the SLEEP terminal and V<sub>DD</sub>.



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#### **FUNCTIONAL DESCRIPTION** (continued)

**Current Sensing.** To minimize inaccuracies in sensing the  $I_{TRIP}$  current level, which may be caused by ground trace IR drops, the sense resistor should have an independent ground return to the ground terminal of the device. For low-value sense resistors the IR drops in the PCB sense resistor's traces can be significant and should be taken into account. The use of sockets should be avoided as they can introduce variation in  $R_{\rm S}$  due to their contact resistance.

The maximum value of  $R_S$  is given as  $R_S = 0.5/I_{TRIP}$ .

**Thermal Protection.** Circuitry turns off all drivers when the junction temperature reaches 165°C typically. It is intended only to protect the device from failures due to excessive junction temperatures and should not imply that output short circuits are permitted. Thermal shutdown has a hysteresis of approximately 15°C.

**Layout.** A star ground system located close to the driver is recommended. The printed wiring board should use a heavy ground plane. For optimum electrical and thermal performance, the driver should be soldered directly onto the board. The ground side of  $R_{\rm S}$  should have an individual path to the ground terminals of the device. This path should be as short as is possible physically and should not have any other components connected to it. It is recommended that a 0.1  $\mu$ F capacitor be placed between SENSE and ground as close to the device as possible; the load supply terminal,  $V_{\rm BB}$ , should be decoupled with an electrolytic capacitor (> 47  $\mu$ F is recommended) placed as close to the device as is possible. On the 28-lead TSSOP package, the copper ground plane located under the exposed thermal pad is typically used as a star ground.



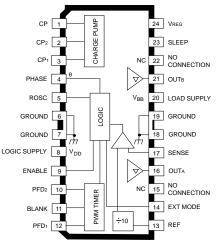
## A3959

# DMOS Full-Bridge PWM Motor Driver

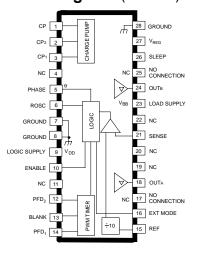
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# Package B (DIP) CP2 1 CHARGE PUMP 24 CP CP1 2 23 VREG PHASE 3 6 22 SLEEP ROSC 4 21 OUTB GROUND 5 7 77 19 GROUND GROUND 7 77 17 SENSE LOGIC 9 VDD 16 OUTA ENABLE 10 14 REF BLANK 12 PWM TIMER 13 PFD1

## Package LB (SOIC)



## Package LP (TSSOP)



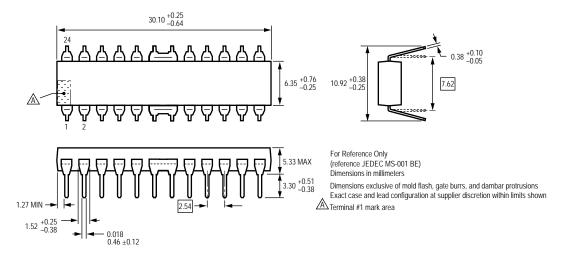
#### **Terminal List**

Terminal Name	Terminal Description	B (DIP)	LB (SOIC)	LP (TSSOP)
СР	Reservoir capacitor (typically 0.22 µF)	24	1	1
CP1 & CP2	The charge pump capacitor (typically 0.22 µF)	1 & 2	2 & 3	2 & 3
NC	No (internal) connection	_	_	4
PHASE	Logic input for direction control	3	4	5
ROSC	Oscillator resistor	4	5	6
GROUND	Grounds	5, 6, 7, 8*	6, 7	7, 8*
LOGIC SUPPLY	VDD, the low voltage (typically 5 V) supply	9	8	9
ENABLE	Logic input for enable control	10	9	10
NC	No (internal) connection	_	_	11
PFD2	Logic-level input for fast decay	11	10	12
BLANK	Logic-level input for blanking control	12	11	13
PFD1	Logic-level input for fast decay	13	12	14
REF	VREF, the load current reference input voltage	14	13	15
EXT MODE	Logic input for PWM mode control	15	14	16
NO CONNECT	No (Internal) connection	_	15	17
OUTA	One of two DMOS bridge outputs to the motor	16	16	18
NC	No (internal) connection	_	_	19, 20
SENSE	Sense resistor	17	17	21
NC	No (internal) connection	_	_	22
GROUND	Grounds	18, 19*	18, 19	_
LOAD SUPPLY	VBB, the high-current, 9.5 V to 50 V, motor supply	20	20	23
OUTB	One of two DMOS bridge outputs to the motor	21	21	24
NO CONNECT	No (Internal) connection	_	22	25
SLEEP	Logic-level Input for sleep operation	22	23	26
VREG	Regulator decoupling capacitor (typically 0.22 µF)	23	24	27
GROUND	Ground	_	_	28*

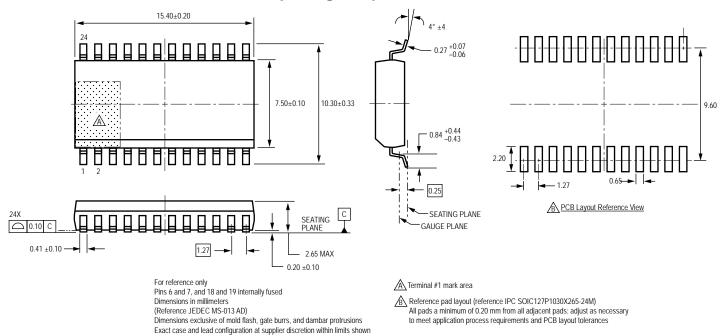
<sup>\*</sup> For the B (DIP) package only, there is an indeterminate resistance between the substrate grounds (pins 6, 7, 18, and 19) and the grounds at pins 5 and 8. Pins 5 and 8, and 6, 7, 18, or 19 must be connected together externally. For the LP (TSSOP) package, the grounds at terminals 7, 8, and 28 should be connected together at the exposed pad beneath the device.



## B package 24-pin DIP

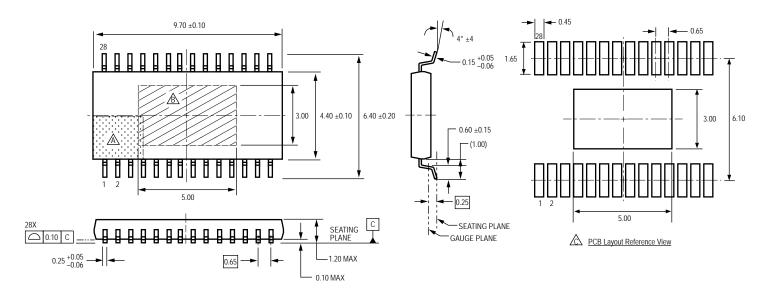


## LB package 24-pin SOICW





## LP package 28-pin TSSOP



For reference only (reference JEDEC MO-153 AET)

Dimensions in millimeters

Dimensions exclusive of mold flash, gate burrs, and dambar protrusions Exact case and lead configuration at supplier discretion within limits shown

A Terminal #1 mark area

A Exposed thermal pad (bottom surface)

Reference land pattern layout (reference IPC7351 SOP65P640X120-29CM);
All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances; when mounting on a multilayer PCB, thermal vias at the exposed thermal pad land can improve thermal dissipation (reference EIA/JEDEC Standard JESD51-5)

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